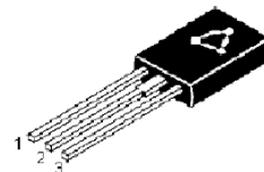


Medium Power Transistor TO-126



Pin Configuration:

1. Emitter
2. Collector
3. Base

Feature:

- Epitaxial Silicon Power Transistors
- Intended for use in Medium Power Linear Switching Applications

Absolute Maximum Ratings

Description	Symbol	BD237	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	
Collector Emitter Voltage ($R_{BE} = 1K$)	V_{CER}	100	
Emitter Base Voltage	V_{EBO}	5	
Collector Current	I_C	2	A
Collector Peak Current	I_{CM}	6	
Power Dissipation at $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	25	W
Power Dissipation at $T_a = 25^\circ C$		1.25 10	W mW/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ C$

Thermal Characteristics

Junction to Case	$R_{th(j-c)}$	100	$^\circ C/W$
Junction to Ambient in Free Air	$R_{th(j-a)}$	4.16	

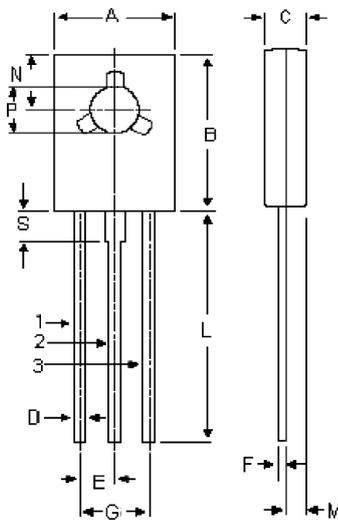
Medium Power Transistor TO-126



Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless specified otherwise)

Description	Symbol	Test Condition	Min.	Typical	Max.	Unit
Collector Cut off Current	I_{CBO}	$V_{CB} = 100\text{V}, I_E = 0$ $T_C = 150^\circ\text{C}$ $V_{CB} = 100\text{V}, I_E = 0$	-	-	100 2	μA mA
Emitter Cut off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$	-	-	1	mA
Collector Emitter Sustaining Voltage	* $V_{CEO(sus)}$	$I_C = 0.1\text{A}, I_B = 0$	80	-	-	V
Collector Emitter Saturation Voltage	* $V_{CEO(sat)}$	$I_C = 1\text{A}, I_B = 0.1\text{A}$	-	-	0.6	
Base Emitter Voltage	* $V_{BE(on)}$	$I_C = 1\text{A}, V_{CE} = 2\text{V}$	-	-	1.3	
DC Current Gain	* h_{FE}	$I_C = 150\text{mA}, V_{CE} = 2\text{V}$ $I_C = 1\text{A}, V_{CE} = 2\text{V}$	40 25	-	-	-
Current Gain Bandwidth Product	f_T	$I_C = 250\text{mA}, V_{CE} = 10\text{V}$	3	-	-	MHz
* h_{FE1}/h_{FE2}	Matched Pairs	$I_C = 250\text{mA}, V_{CE} = 2\text{V}$	-	1.6	-	-

*Pulse Test : Pulse Width = 300 μs , Duty Cycle = 1.5%.



Pin Configuration:

1. Emitter
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Dimensions	Min.	Max.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 (Typical)	
F	0.49	0.75
G	4.5 (Typical)	
L	15.7 (Typical)	
M	1.27 (Typical)	
N	3.75 (Typical)	
P	3	3.2
S	2.5 (Typical)	

Dimensions : Millimetres

Part Number Table

Description	Part Number
Transistor, NPN, TO-126	BD237

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